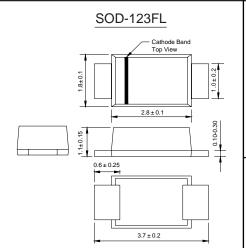


SM4001PL THRU SM4007PL

SUR FACE MOUNT GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere



Dimensions in millimeters

FEATURES

- Glass passivated device
- ◆ Ideal for surface mouted applications
- Low reverse leakage
- Metallurgically bonded construction
- High temperature soldering guaranteed: 250°C/10 seconds,0.375"(9.5mm) lead length, 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body over passivated chip

Terminals: Solderable per MIL-STD-750,

Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.0007 ounce, 0.02 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	4001	4002	4003	4004	4005	4006	4007	UNITS
MDD Catalog Number		A1	A2	А3	A4	A5	A6	A7	00
Maximum repetitive peak reverse voltage	Vrrm	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	VRMS	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	VDC	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at Ta=65°C (NOTE 1)	l(AV)	1.0							Amp
Peak forward surge current									
8.3ms single half sine-wave superimposed on	IFSM 25.0							Amps	
rated load (JEDEC Method) TL=25°C									
Maximum instantaneous forward voltage at 1.0A	VF	V _F 1.1							Volts
Maximum DC reverse current Ta=25℃		10.0 50.0							μА
at rated DC blocking voltage Ta=125℃	l _R								
Typical junction capacitance (NOTE 2)	Сı	C _J 4							pF
Typical thermal resistance (NOTE 3)	Reja	180							°C/W
Operating junction and storage temperature range	ТЈ,Тѕтс	-55 to +150							°C

Note: 1. Averaged over any 20ms period.

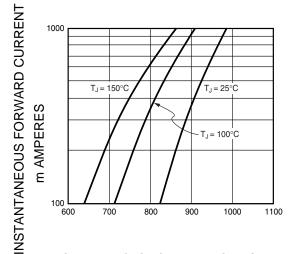
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. Thermal resistance from junction to ambient at 0.375" (9.5mm)lead length, P.C.B. mounted



RATINGS AND CHARACTERISTIC CURVES SM4001PL THRU SM4007PL

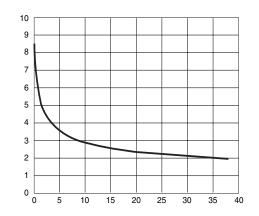
FIG.1 -TYPICAL FORWARD CHARACTERISTIC



INSTANTANEOUS FORWARD VOLTAGE, mV

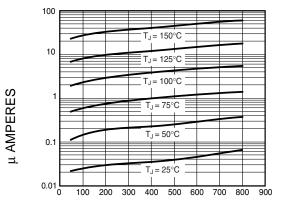
FIG.2 - TYPICAL JUNCTION CAPACITANCE

CAPACITANCE, pF



REVERSE VOLTAGE, VOLTS

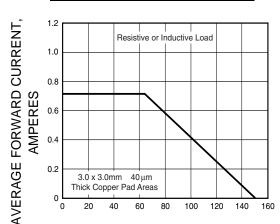
FIG.3 – TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS



INSTANTANEOUS REVERSE CURRENT

INSTANTANEOUS REVERSE VOLTAGE,V

FIG.4 - FORWARD DERATING CURVE



AMBIENT TEMPERATURED

The cruve graph is for reference only, can't be the basis for judgment(曲线图仅供参考)!



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